



Diamond Sensors for Future High Energy Experiments

Felix Bachmair on behalf of the RD42 collaboration



The RD42 Collaboration

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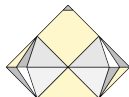
129 Participants

31 Institutes



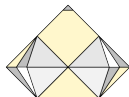
Overview

- Diamond as a sensor material
 - Newest developments in chemical vapor deposition (CVD) diamonds
 - Radiation tolerance
- Overview of diamond detectors in HEP
- Latest experiences for
 - CMS PLT pilot run
 - ATLAS DBM
- 3D diamond detectors
 - Single-crystalline (sc)CVD diamond
 - Polycrystalline (p)CVD diamond



Why diamond?

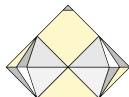
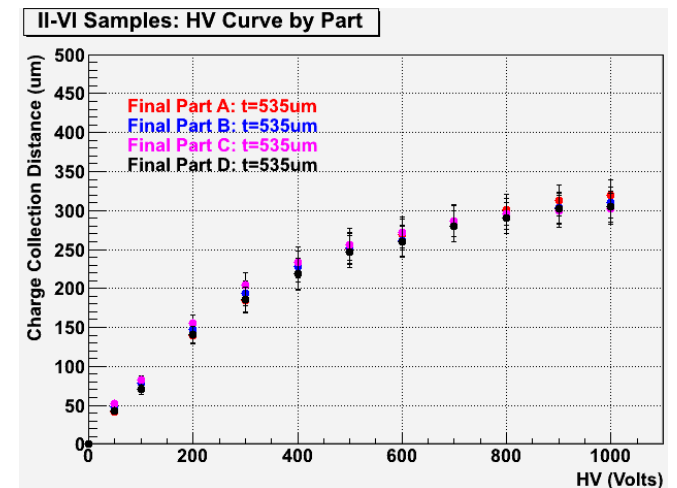
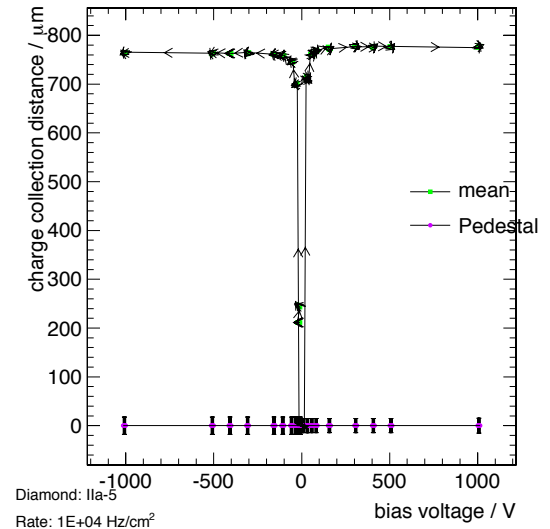
- advantages of diamonds w/r/t silicon
 - large displacement energy
 - Radiation hard
 - large bandgap
 - less leakage current & noise
 - high thermal conductivity
 - less cooling, good heatspread
- there are some disadvantages though
 - Large bandgap
 - less signal
 - Size of diamonds (scCVD)
 - Material more expensive than Si



Diamond Manufacturers

- In the past diamonds via DDL from ElementSix (De Beers)
 - DDL out of business, now directly via ElementSix
- New suppliers
 - Ila-Technologies (scCVD)
 - II-VI Incorporated (pCVD)
- Ila has delivered O(10) samples for evaluation
 - committed their self to
 - Further improvement of material
 - pCVD growth
- II-VI improved quality of pCVD over the last years
 - Delivered growing number of final finished parts to CMS and ATLAS
 - Now typically deliver 275 - 300 μm collection distance

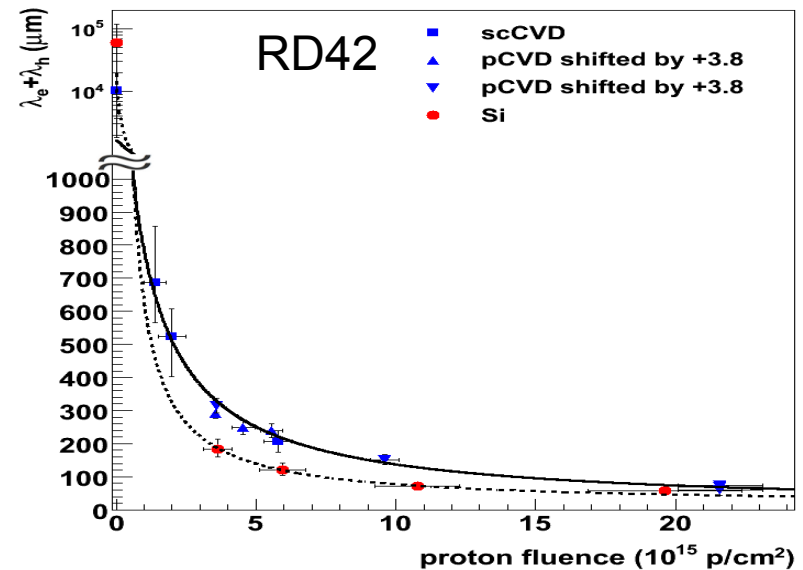
Ila scCVD diamond
with thickness $\sim 775 \mu\text{m}$



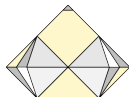
Radiation Hardness

- 24 GeV protons
- $k_\lambda = 0.62 \pm 0.07 \times 10^{-18} \mu\text{m}^{-1}\text{cm}^{-2}$
- Polycrystalline diamond sample offset by $\Phi \sim 5 \times 10^{15}$ to account for existing traps.
- Poly and single crystal diamond show consistent damage constants.

$$\lambda_{e/h}(\Phi) = \frac{\lambda_0}{1 + \lambda_0 \cdot k \cdot \Phi}$$

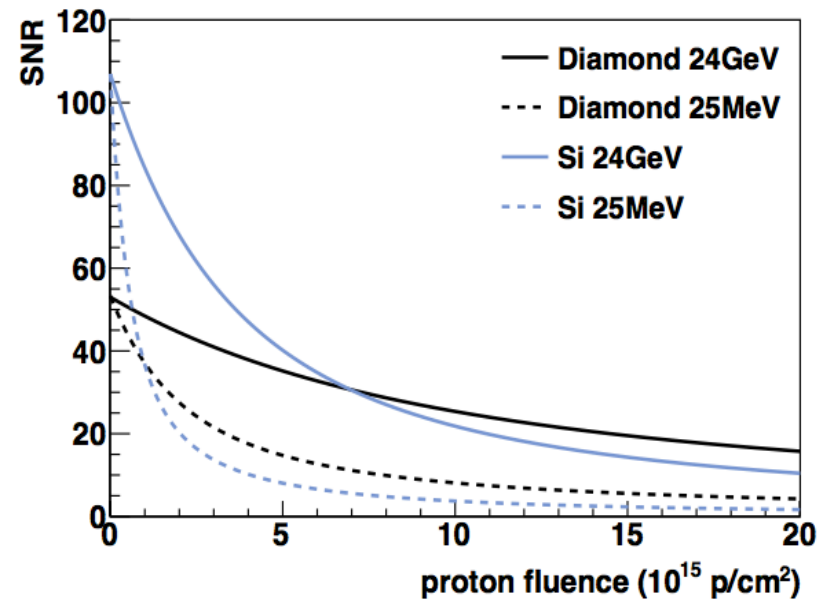


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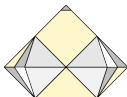


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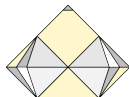
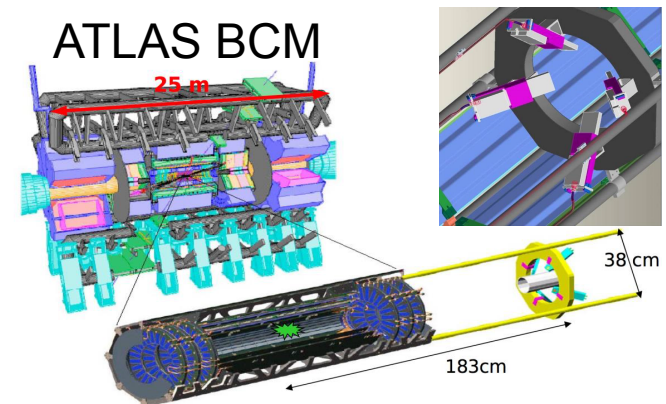
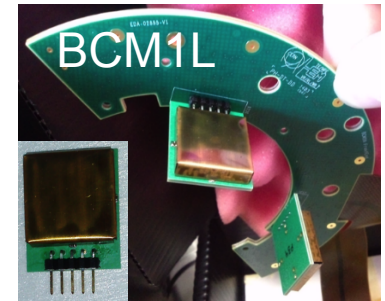


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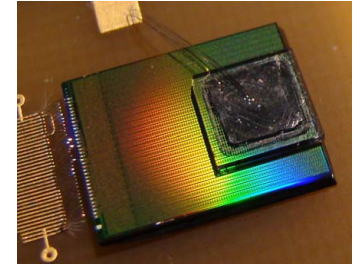


More high energy diamond experiments

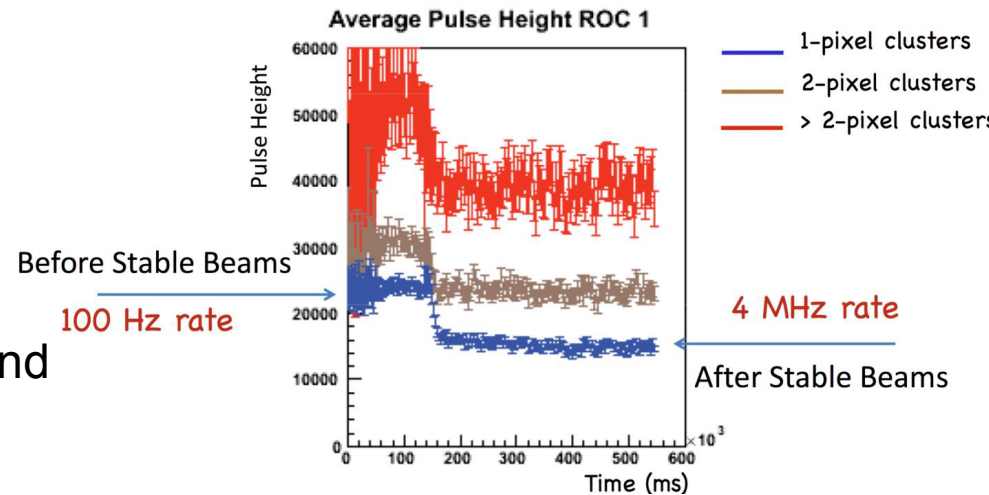
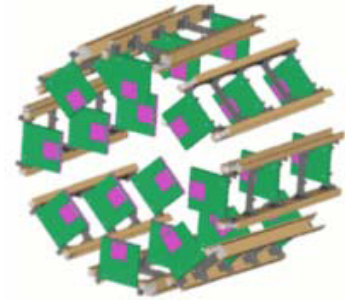
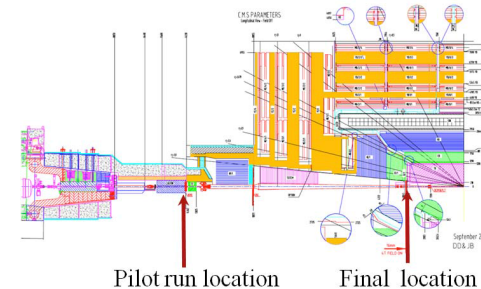
- CMS:
 - BCM1F: for online background and luminosity measurements
 - 24 scCVD diamond sensors, 48 Channels
 - Fast MIP counter, trigger-less readout
 - BCM1L/BCM2L: Beam abort system
 - Based pCVD diamond sensors
- ATLAS:
 - BCM:
 - 4 x 2 pCVD diamonds on each side
 - Single particle counting with $\sigma = 0.7\text{ns}$.



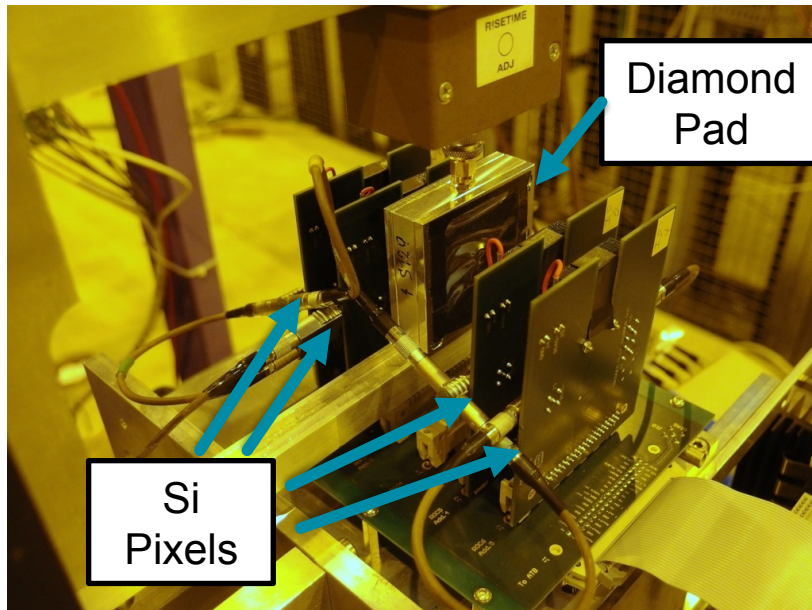
CMS Pixel Luminosity Telescope (PLT)



- High precision bunch-by-bunch luminosity measurement with an array of eight 3-plane telescopes
 - Pilot Run: Diamond sensors
 - Final Installation: Silicon sensors
- Pilot Run while LHC Run 1 in Castor region: 14.5m from IP
 - Total exposure 20fb^{-1}
 - $5 \times 10^{13} \text{ n/cm}^2$ and 5×10^{13} charged hadrons/cm²
- In the Pilot Run:
 - strong rate dependency for this diamonds after a small amount of irradiation
- Major effort was started to understand this issue



PSI beam test campaign

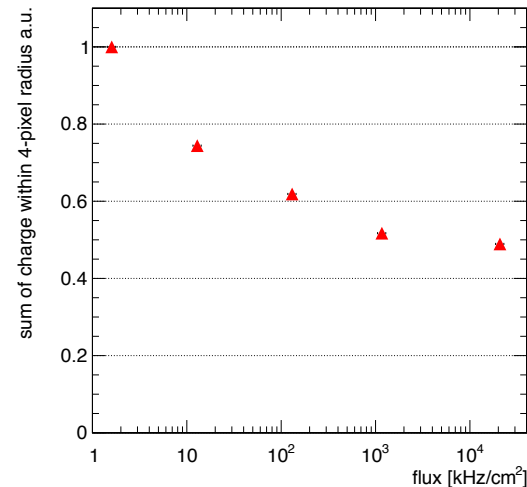
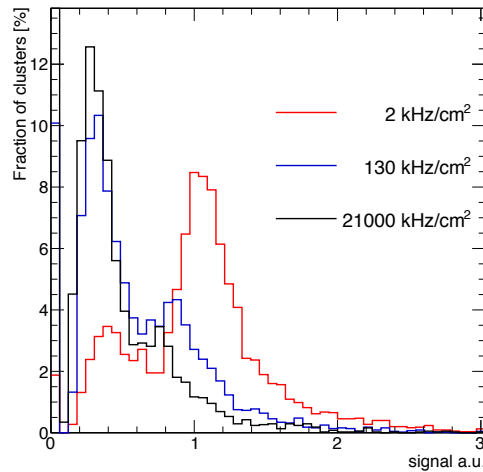


- Multiple beam tests at PSI
- Compact Si telescope based on CMS pixel chip PSI46v2
 - Scalable trigger size
 - Readout of pad detectors with Amplifier + DRS4 Evaluation board
- Testing pCVD and scCVD
 - irradiated/non-irradiated/ Pilot Run irradiated
 - Pad detectors:
 - Quick detector fabrication and turn around
 - study sensors w/o threshold effect
 - Pixel detectors:
 - Study effects of pixel threshold
 - Study effects of pixel charge sharing

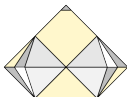
PSI	Paul Scherrer Institute
Beamline	HIPA/PiM1
Beam Energy	250 MeV/c
Particles	Mostly π^+
Flux	$O(1\text{kHz/cm}^2) - O(10\text{ MHz/cm}^2)$

Pixel Results for rate studies

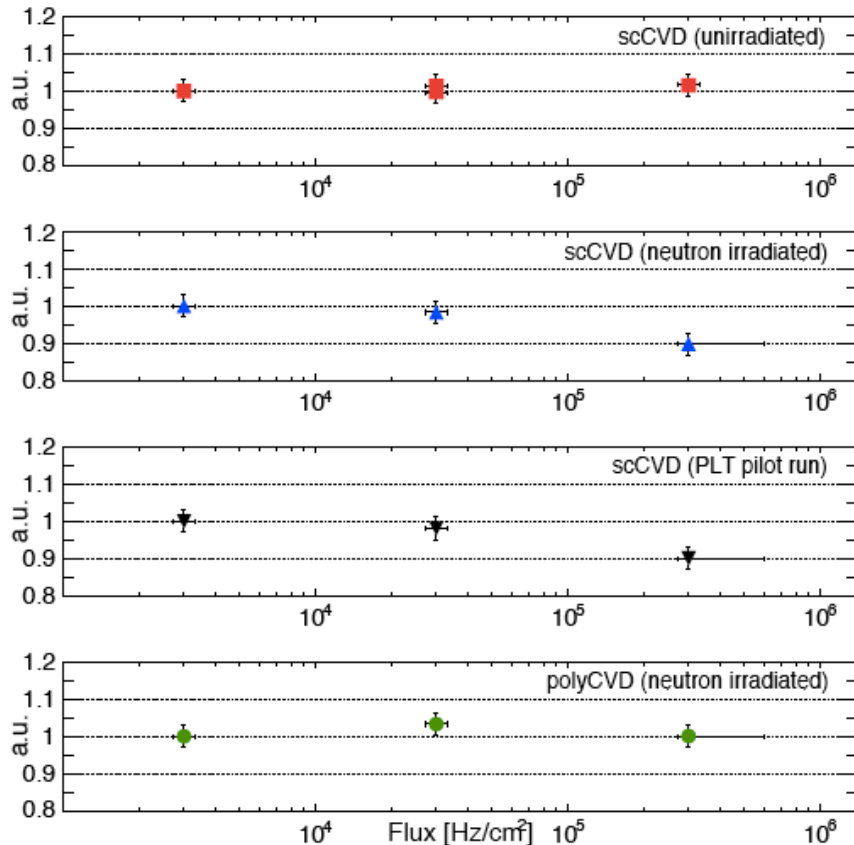
- Testing irradiated scCVD pixel detector
 - Using PSI46v2 readout chip
 - 5×10^{13} n/cm² and 5×10^{13} charged hadrons/cm² (PLT pilot run diamond)



- 50% drop in charge with flux
- Similar effect as seen in PLT pilot run



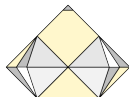
PAD Results for rate studies



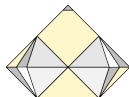
- scCVD unirradiated and pCVD irradiated show less than few % signal variation up to $O(\text{MHz}/\text{cm}^2)$
- scCVD irradiated with neutrons and in CMS (PLT pilot run 2012) show similar behavior:
 - $\sim 10\%$ drop in signal at flux $> 100 \text{ kHz}/\text{cm}^2$
- pCVD does not show a rate effect

Rate dependency summary

- Also tested irradiated/unirradiated scCVD diamonds from Ila Technology
 - Seems to show less rate dependence than E6 diamonds
- Investigation of rate dependencies is continuing with an improved readout system with
 - Faster amplifiers for PAD readout
 - Lower threshold ROC for Pixel measurements
 - Longer data taking capabilities
- Up to now:
 - **No rate dependence for pCVD diamonds** irradiated with $5e13$ neutrons/cm² up to 2 MHz/cm²
 - Rate dependence seems to be a growth dependent



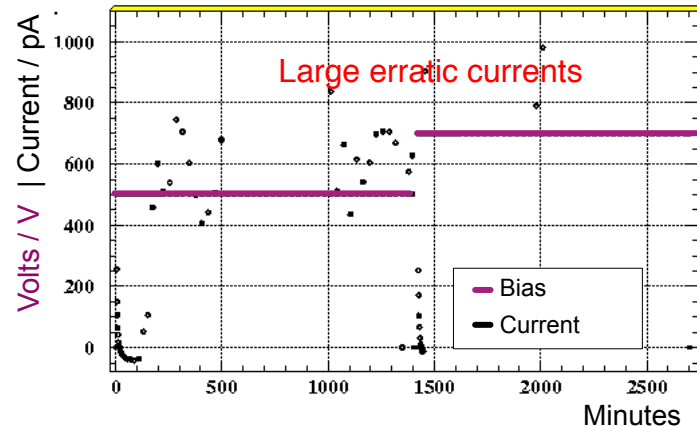
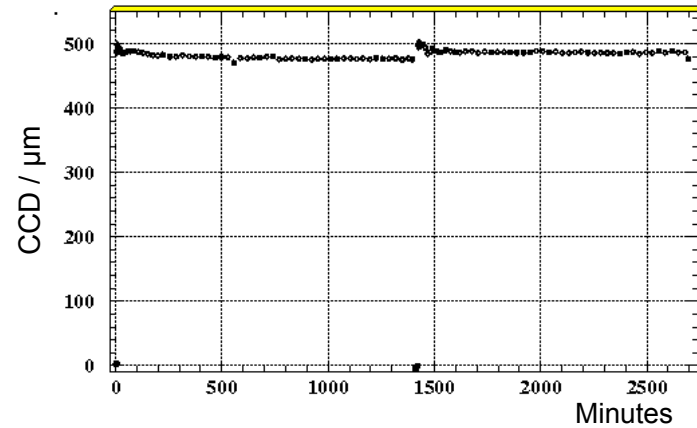
Effect of surface treatment on a leakage current



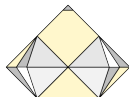
Lessons learned – leakage current

- Observed large erratic currents for several diamonds
 - This diamonds could not hold high bias fields
 - Some scCVD diamonds were not collecting full charge @ $1\text{V}/\mu\text{m}$
 - Different results for positive and negative polarity

PLTS49 run20528 2013/01/28 15.18



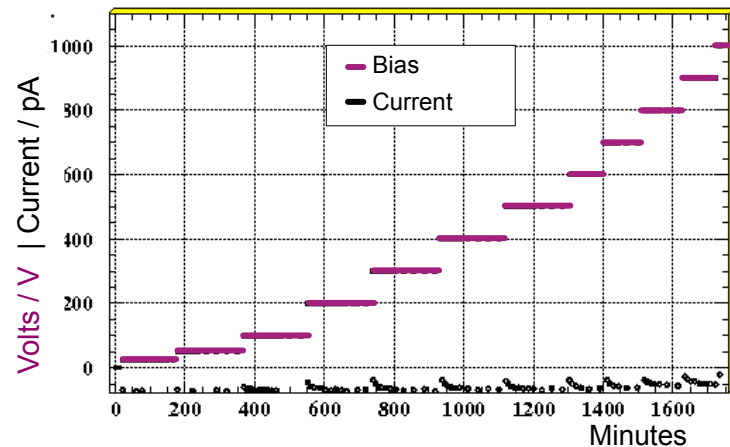
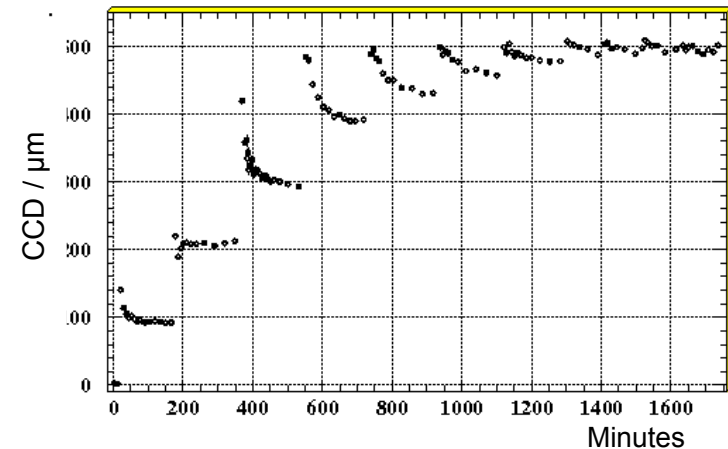
Can't go above 700V



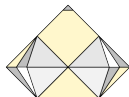
Lesson learned – leakage current

- Surface treatment with reactive ion etching (RIE)
 - Fixing HV problems
 - More stable currents
 - Higher voltages/ electric fields
 - More symmetric charge collection
 - Improving charge collection

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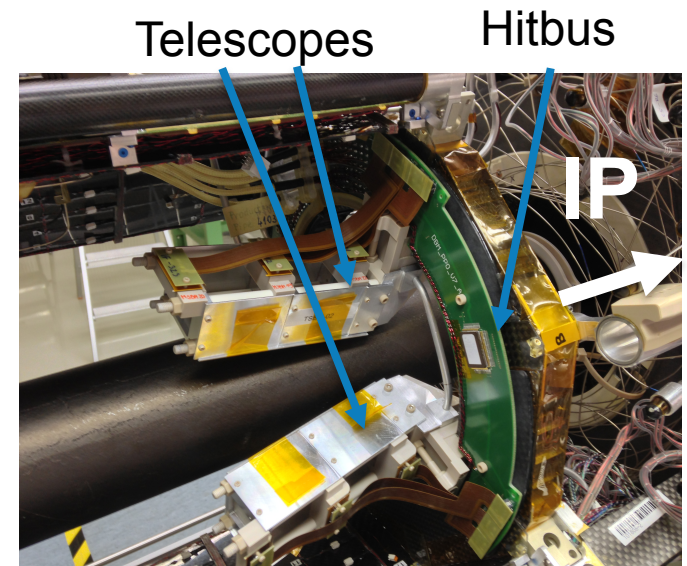
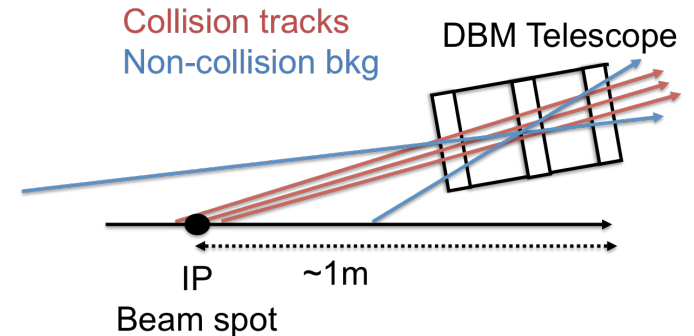


Can go
to
1000V



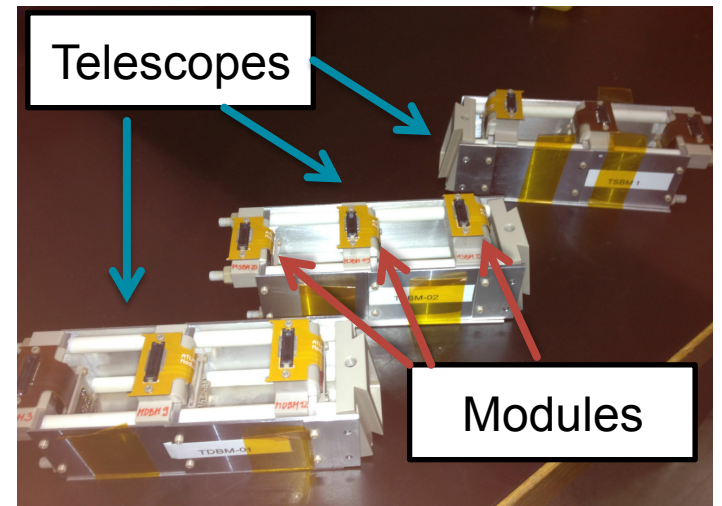
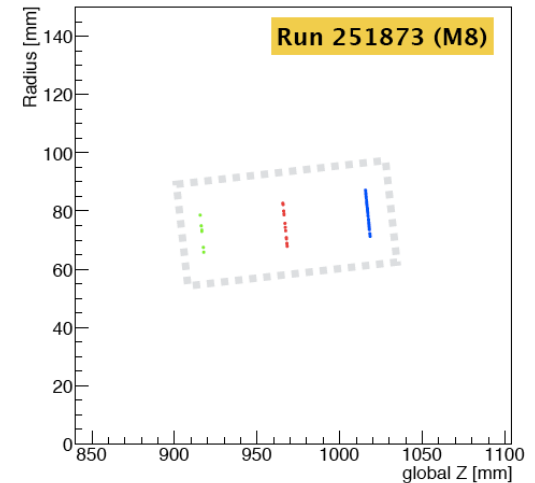
ATLAS Diamond Beam Monitor (DBM)

- Purpose:
 - Bunch-by-bunch luminosity monitor (aim <math><1\%</math> per BC per LB)
 - Bunch-by-bunch beam spot monitor
 - Pixelated sensors allow (limited) tracking to distinguish collision tracks from beam halo
- Design:
 - 4 telescopes of three FE-I4 modules at $\eta \cong 3.2$ per side \rightarrow 24 modules
- On each side
 - 3 diamond telescopes with diamonds from 2 suppliers (E6 & II-VI) bump bonded at IZM
 - 1 silicon telescope

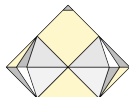


DBM status

- Powered since early February for ATLAS cosmic/commissioning runs
 - Included in ATLAS central data-taking since mid of February
- Sensors biased at
 - 50 V (silicon telescopes)
 - 500 V (diamond telescopes)
- Thresholds tuned to 2500e for diamond
 - Plan to tune to 1500e
- New experiences with
 - bump bonding
 - Installation

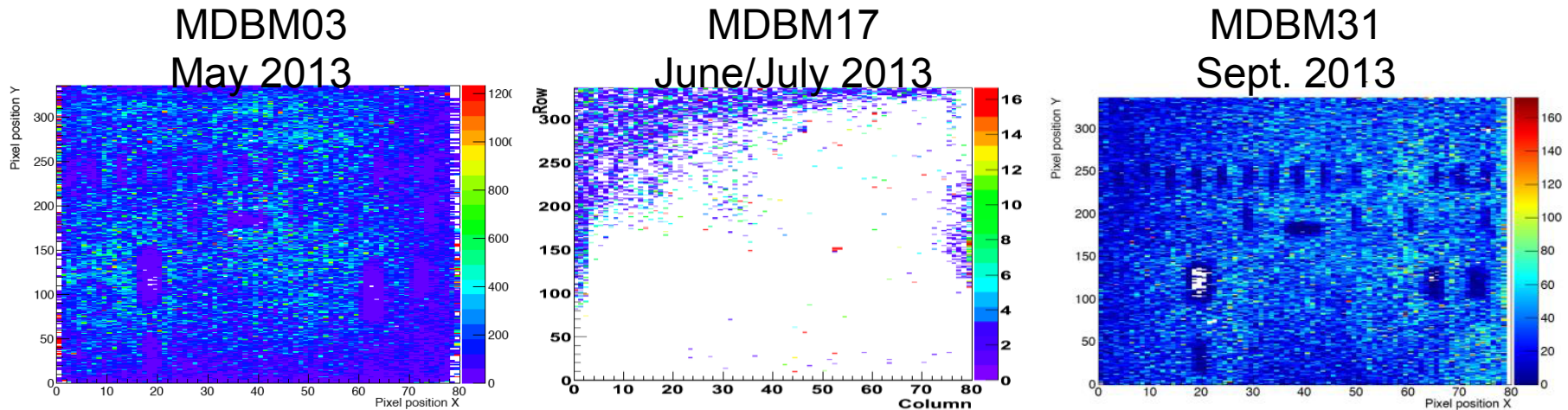


Experience DBM Bump Bonding

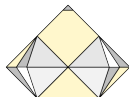


Lessons learned – Bump bonding issues

- FE-I4 – Biggest Pixel chip ever bump bonded to a diamond
 - 26880 pixels with an active area of 341 mm²
- Bump bonding of diamonds in four batches

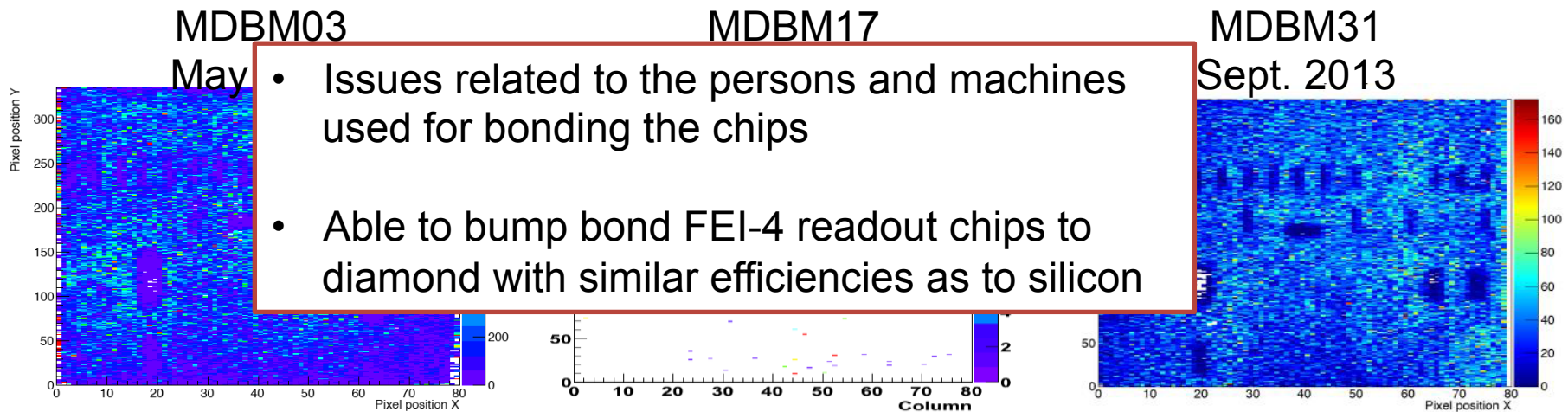


- Batch 1 & 4: Similar bump bond efficiencies as for silicon
- Batch 2 & 3: Low bump bond efficiencies

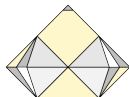


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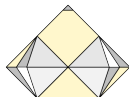


Experience DBM Installation

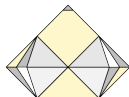


Lesson learned – installation issues

- ‘Lost’ 3 DBM modules in 2 telescopes during operation
 - 1 diamond module
 - 2 Si modules
- Left modules in an unconfigured state
- Probably wire bonds broke due to high currents and magnetic field
- Investigation is in progress but definitely not a sensor related issue



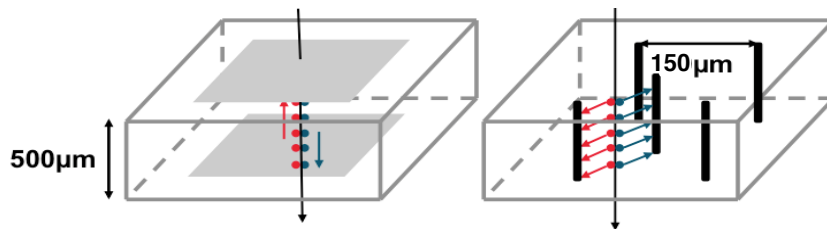
3D diamond detectors



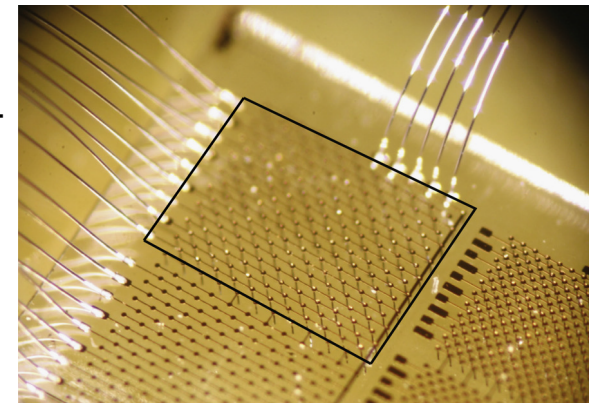
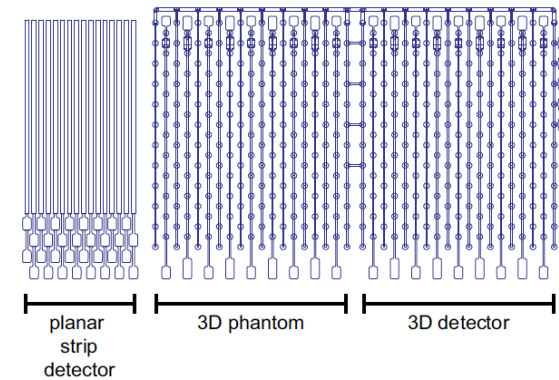
3D diamond detectors

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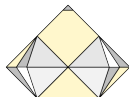
- 3D geometry to shorten the drift distances



- For 3D geometry using a femto second laser (100fs) with a wavelength of 800 nm
 - phase change of diamond into a combination of diamond-like carbon, amorphous carbon and graphite
- Sizes:
 - Planar strip pitch 50 μm
 - 3D Cell size: 150 x 150 μm²
- Optical and resistivity measurements show a yield for micromachining columns of ~ 90 %

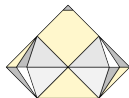
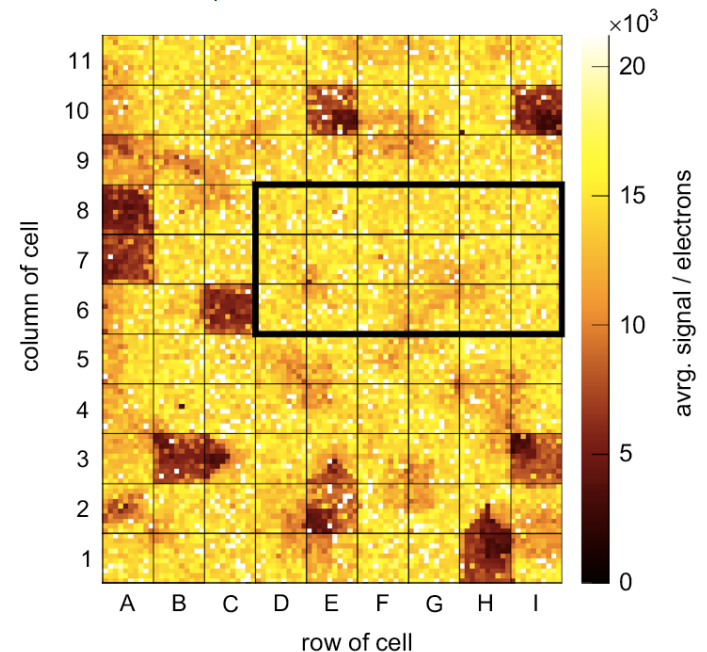
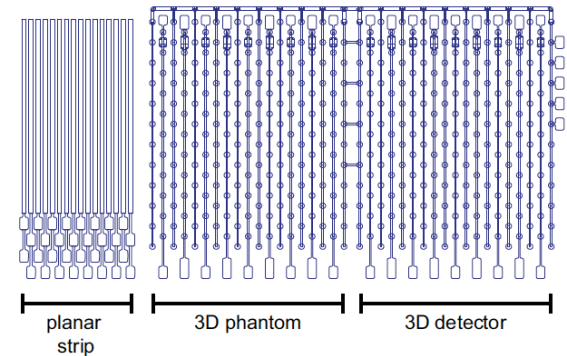


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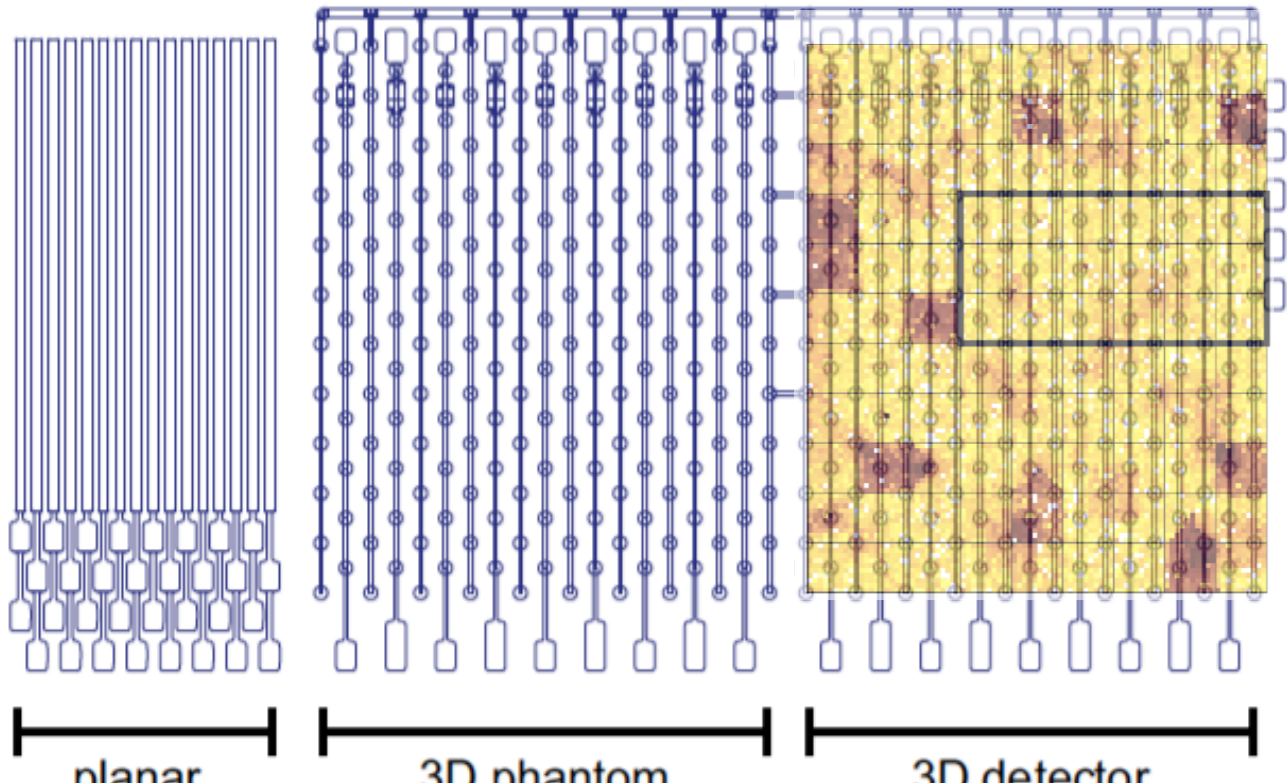
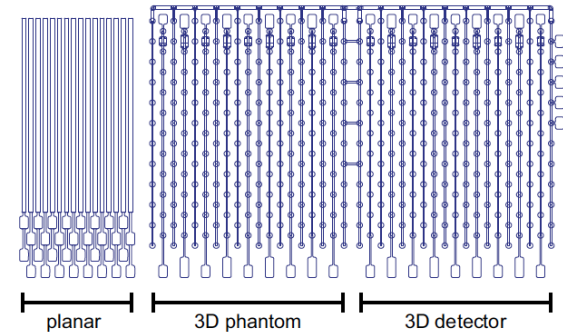
3D diamond detectors

- 3 different regions on one diamond for comparison
 - Planar strip @ 500V, pitch 50 μm
 - 3D phantom @ 25V, size 150 x 150 μm^2
 - 3D detector @ 25V, size 150 x 150 μm^2
- Missing charge around ~ 9 broken readout columns
 - In agreement with other measurements
- See effects of missing bias columns



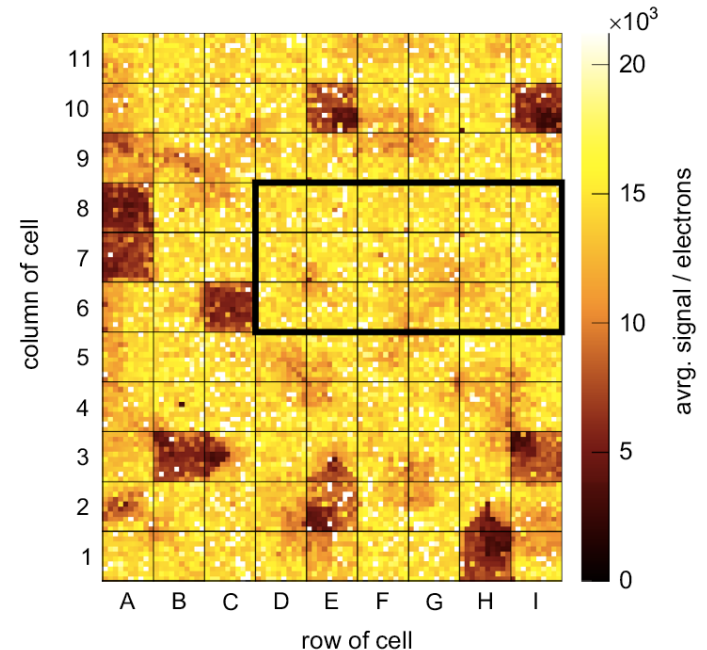
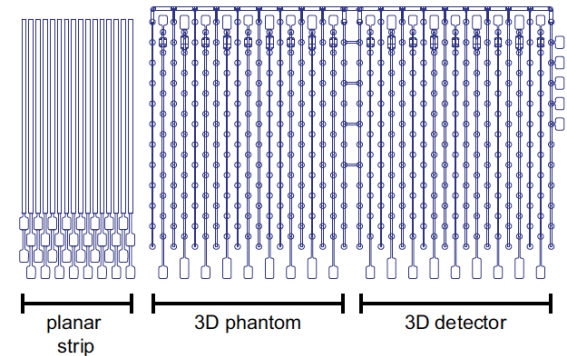
3D diamond detectors

- 3 different regions on one diamond for comparison
 - Planar strip @ 500V, pitch 50 μm
 - 3D phantom
 - 3D detector
- Missing broken
 - In agreement
 - measured
- See efficiency column



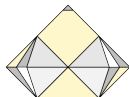
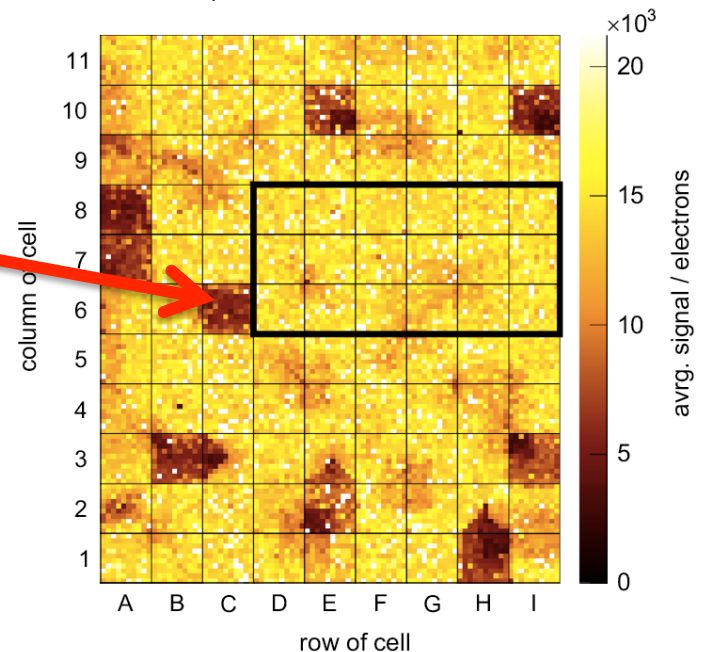
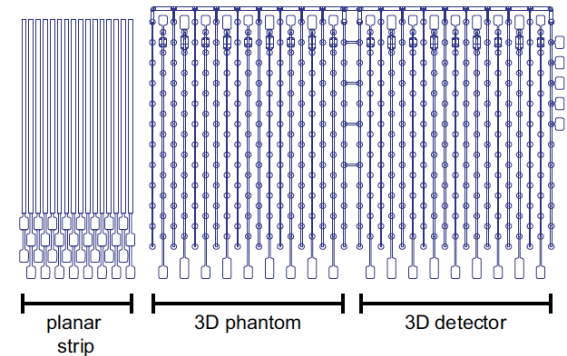
3D diamond detectors

- 3 different regions on one diamond for comparison
 - Planar strip @ 500V, pitch 50 μm
 - 3D phantom @ 25V, size 150 x 150 μm^2
 - 3D detector @ 25V, size 150 x 150 μm^2
- Missing charge around ~ 9 broken readout columns
 - In agreement with other measurements
- See effects of missing bias columns



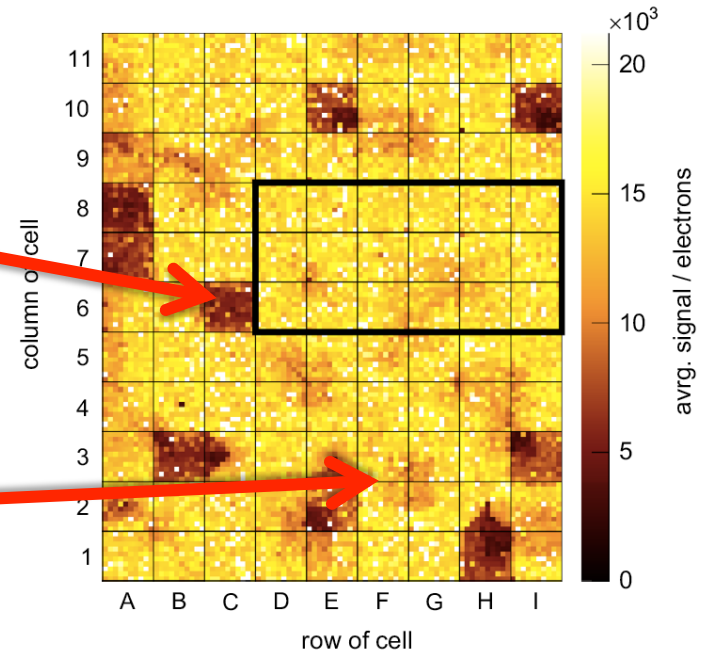
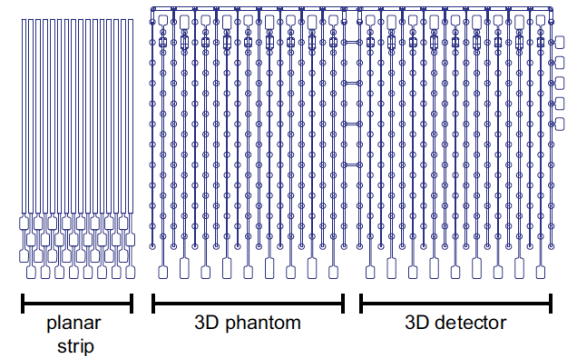
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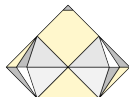
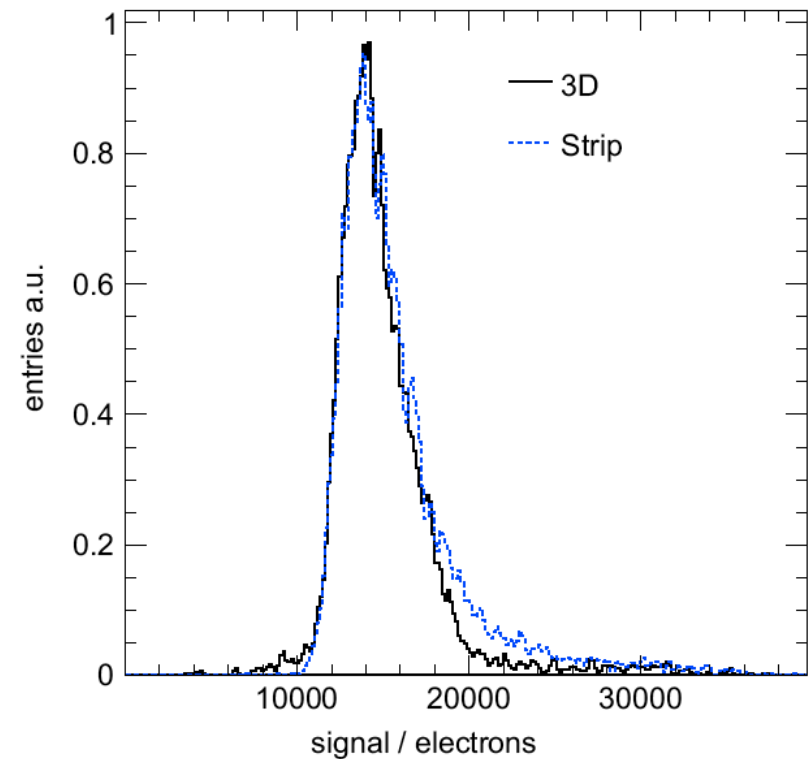
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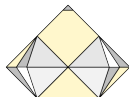
3D diamond detectors

- Remarkable agreement between signal in 3D and planar strip geometry for a good cell region
- full charge at lower avg. E Field



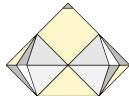
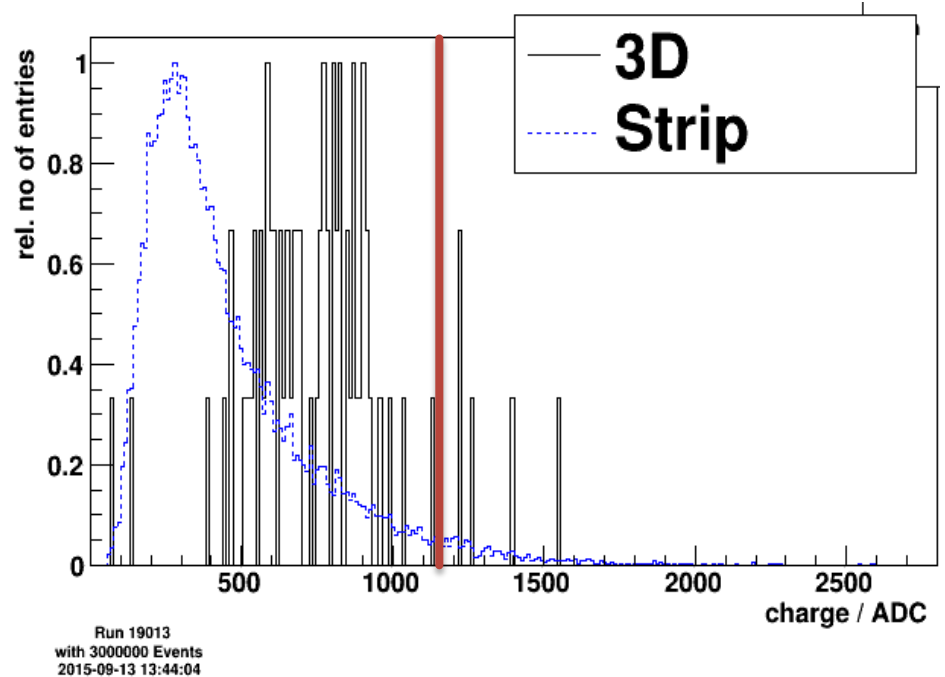
3D pCVD diamond detectors

- 3D pCVD diamond has been tested in beam tests at CERN this summer
- Same layout/mask as for 3D scCVD diamond with Planar Strip/3D-Phantom/3D-Detector
 - Smaller yield in fabrication of columns than for scCVD
 - Smaller yield in contacting the columns with the metallization than for scCVD
- Preliminary result without calibration to electrons
 - 3D-Detector & 3D-Phantom biased @ 75V, planar strip @ 500V
 - Comparison between 3D detector and planar strip
 - Looking at single working cells



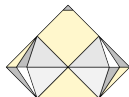
Poly 3D

- Red line: estimate for MP of full charge collection (500 μm)
- Collecting more charge than planar strip detector
- ~ 77% of Full charge collection @ 75V
- Highest charge collection ever measured for pCVD diamonds



Summary

- New diamond suppliers, IIa & II-VI, improved situation on the market
- Quality of diamonds has improved strongly over the last years
 - Now reaching 275 - 300 μm CD in pCVD diamonds
- New experiences in using diamonds on bigger scales in CMS PLT Pilot Run and Atlas DBM
 - Most problems has been understood and solved
- Rate dependency still under study,
 - seems to be growth dependent
 - We did not observed a rate dependence for pCVD diamonds
- 3D diamond detectors show a great promise
 - 3D pCVD shows 2.5x the charge of a planar pCVD strip detector at 75V.



Outlook

- Further improvement of diamond quality in cooperation with suppliers
- Continue Rate studies with improved setup
 - Faster amplifiers for PAD readout
 - Lower threshold ROC for Pixel measurements
 - Longer data taking capabilities
- Working on thinner diamond detectors
- R&D for HL-LHC: innermost layer of Tracker
- R&D on 3D devices
 - Improve fabrication of 3D device
 - Higher yield
 - Bigger detectors
 - Test different structures
 - Studies of irradiated 3D CVD diamonds
 - Measure 3D pCVD at higher bias voltages.

